

Antonin Fejfar

List of Publications by Year in Descending Order

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The third column is the impact factor (IF) of the journal, and the fourth column is the number of citations of the article.

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|--------------------|-------------------------|----------------|-----------------|
| 150 papers | 2,415 citations | 24 h-index | 42 g-index |
| 162 ext. papers | 2,645 ext. citations | 3.3 avg, IF | 4.31 L-index |

| # | Paper | IF | Citations |
|-----|---|------|-----------|
| 150 | Doping of the hydrogen-passivated Si(100) electronic structure through carborane adsorption studied using density functional theory. <i>Physical Chemistry Chemical Physics</i> , 2021 , 23, 20379-20387 | 3.6 | 0 |
| 149 | Nanoscale Study of the Hole-Selective Passivating Contacts with High Thermal Budget Using C-AFM Tomography. <i>ACS Applied Materials & Interfaces</i> , 2021 , 13, 9994-10000 | 9.5 | 0 |
| 148 | Impact of Cation Multiplicity on Halide Perovskite Defect Densities and Solar Cell Voltages. <i>Journal of Physical Chemistry C</i> , 2020 , 124, 27333-27339 | 3.8 | 7 |
| 147 | Nucleation and growth of metal-catalyzed silicon nanowires under plasma. <i>Nanotechnology</i> , 2020 , 31, 225601 | 3.4 | 1 |
| 146 | Transferless Inverted Graphene/Silicon Heterostructures Prepared by Plasma-Enhanced Chemical Vapor Deposition of Amorphous Silicon on CVD Graphene. <i>Nanomaterials</i> , 2020 , 10, | 5.4 | 1 |
| 145 | Growth defects in WC:H layers for tribological applications. <i>Vacuum</i> , 2020 , 178, 109372 | 3.7 | |
| 144 | Temperature Dependence of the Urbach Energy in Lead Iodide Perovskites. <i>Journal of Physical Chemistry Letters</i> , 2019 , 10, 1368-1373 | 6.4 | 116 |
| 143 | Comparative study of catalyst-induced doping and metal incorporation in silicon nanowires. <i>Applied Physics Letters</i> , 2019 , 114, 132103 | 3.4 | 6 |
| 142 | Tuning of the gold work function by carborane films studied using density functional theory. <i>Physical Chemistry Chemical Physics</i> , 2019 , 21, 6178-6185 | 3.6 | 1 |
| 141 | Sculpturing graphene wrinkle patterns into compliant substrates. <i>Carbon</i> , 2019 , 146, 772-778 | 10.4 | 9 |
| 140 | Effects of nanowire size and geometry on silicon nanowire array thin film solar cells. <i>Journal of Vacuum Science and Technology B: Nanotechnology and Microelectronics</i> , 2018 , 36, 011401 | 1.3 | 3 |
| 139 | Local Photovoltaic Properties of Graphene/Silicon Heterojunctions (Phys. Status Solidi B 12/2018). <i>Physica Status Solidi (B): Basic Research</i> , 2018 , 255, 1870144 | 1.3 | |
| 138 | Local Photovoltaic Properties of Graphene/Silicon Heterojunctions. <i>Physica Status Solidi (B): Basic Research</i> , 2018 , 255, 1800305 | 1.3 | 4 |
| 137 | Local Current Measurements 2018 , 265-301 | | |
| 136 | Direct Imaging of Dopant Distribution in Polycrystalline ZnO Films. <i>ACS Applied Materials & Interfaces</i> , 2017 , 9, 7241-7248 | 9.5 | 7 |
| 135 | Photovoltaic characterization of graphene/silicon Schottky junctions from local and macroscopic perspectives. <i>Chemical Physics Letters</i> , 2017 , 676, 82-88 | 2.5 | 8 |
| 134 | Passivating electron contact based on highly crystalline nanostructured silicon oxide layers for silicon solar cells. <i>Solar Energy Materials and Solar Cells</i> , 2016 , 158, 2-10 | 6.4 | 68 |

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| 133 | Experimental quantification of useful and parasitic absorption of light in plasmon-enhanced thin silicon films for solar cells application. <i>Scientific Reports</i> , 2016 , 6, 22481 | 4.9 | 37 |
| 132 | Role of a-Si:H in lateral growth of crystalline silicon nanowires using Pb and In catalysts. <i>Physica Status Solidi (A) Applications and Materials Science</i> , 2016 , 213, 1821-1825 | 1.6 | 2 |
| 131 | Passivation effect of water vapour on thin film polycrystalline Si solar cells. <i>Physica Status Solidi (A) Applications and Materials Science</i> , 2016 , 213, 1969-1975 | 1.6 | 1 |
| 130 | Adsorption of oriented carborane dipoles on a silver surface. <i>Physica Status Solidi (B): Basic Research</i> , 2016 , 253, 591-600 | 1.3 | 8 |
| 129 | Passivating contacts for silicon solar cells with 800 °C stability based on tunnel-oxide and highly crystalline thin silicon layer 2016 , | | 3 |
| 128 | Profilometry of thin films on rough substrates by Raman spectroscopy. <i>Scientific Reports</i> , 2016 , 6, 37859 | 4.9 | 13 |
| 127 | Thin Film Polycrystalline Silicon Solar Cells Studied by Transient Terahertz Probe Spectroscopy. <i>Energy Procedia</i> , 2016 , 102, 19-26 | 2.3 | |
| 126 | Phosphate content influence on structural, spectroscopic, and lasing properties of Er,Yb-doped potassium-lanthanum phosphate glasses. <i>Optical Engineering</i> , 2016 , 55, 047102 | 1.1 | 3 |
| 125 | Conductivity Mechanisms in Sb-Doped SnO ₂ Nanoparticle Assemblies: DC and Terahertz Regime. <i>Journal of Physical Chemistry C</i> , 2015 , 119, 19485-19495 | 3.8 | 16 |
| 124 | Investigating inhomogeneous electronic properties of radial junction solar cells using correlative microscopy. <i>Japanese Journal of Applied Physics</i> , 2015 , 54, 08KA08 | 1.4 | 7 |
| 123 | Correlative microscopy of radial junction nanowire solar cells using nanoindent position markers. <i>Solar Energy Materials and Solar Cells</i> , 2015 , 135, 106-112 | 6.4 | 11 |
| 122 | Size and Purity Control of HPHT Nanodiamonds down to 1 nm. <i>Journal of Physical Chemistry C</i> , 2015 , 119, 27708-27720 | 3.8 | 112 |
| 121 | Thin film polycrystalline Si solar cells studied in transient regime by optical pump-terahertz probe spectroscopy. <i>Applied Physics Letters</i> , 2015 , 107, 233901 | 3.4 | 4 |
| 120 | Nanoimprint-textured Glass Superstrates for Light Trapping in Crystalline Silicon thin-film Solar Cells. <i>Energy Procedia</i> , 2015 , 84, 118-126 | 2.3 | 4 |
| 119 | Raman Spectroscopy of Organic-Inorganic Halide Perovskites. <i>Journal of Physical Chemistry Letters</i> , 2015 , 6, 401-6 | 6.4 | 182 |
| 118 | Preparation and testing of silicon nanowires. <i>Canadian Journal of Physics</i> , 2014 , 92, 819-821 | 1.1 | 1 |
| 117 | On the effects of hydrogenation of thin film polycrystalline silicon: A key factor to improve heterojunction solar cells. <i>Solar Energy Materials and Solar Cells</i> , 2014 , 122, 31-39 | 6.4 | 17 |
| 116 | Fabrication of SnS quantum dots for solar-cell applications: Issues of capping and doping. <i>Physica Status Solidi (B): Basic Research</i> , 2014 , 251, 1309-1321 | 1.3 | 10 |

- 115 ANNEALING OF POLYCRYSTALLINE THIN FILM SILICON SOLAR CELLS IN WATER VAPOUR AT SUB-ATMOSPHERIC PRESSURES. *Acta Polytechnica*, **2014**, 54, 341-347 1
- 114 Light trapping in thin-film solar cells measured by Raman spectroscopy. *Applied Physics Letters*, **2014**, 105, 111106 3.4 10
- 113 Displacement Interferometry within a Passive Fabry-Perot Cavity **2014**, 891-894
- 112 Modulated surface of single-layer graphene controls cell behavior. *Carbon*, **2014**, 72, 207-214 10.4 9
- 111 Microscopic measurements of variations in local (photo)electronic properties in nanostructured solar cells. *Solar Energy Materials and Solar Cells*, **2013**, 119, 228-234 6.4 9
- 110 Two Simple Classroom Demonstrations for Scanning Probe Microscopy Based on a Macroscopic Analogy. *Journal of Chemical Education*, **2013**, 90, 361-363 2.4 12
- 109 Conductivity measurement of individual SnS nanoparticles by Peak Force AFM. *Materials Research Society Symposia Proceedings*, **2013**, 1557, 1
- 108 Characterization of the mechanical properties of qPlus sensors. *Beilstein Journal of Nanotechnology*, **2013**, 4, 1-9 3 21
- 107 Electrical properties of carbon nanowall films. *Journal of Non-Crystalline Solids*, **2012**, 358, 2548-2551 3.9 9
- 106 Local photoconductivity of microcrystalline silicon thin films excited by 442nm HeCd laser measured by conductive atomic force microscopy. *Journal of Non-Crystalline Solids*, **2012**, 358, 2082-2085 3.9 4
- 105 Conductive atomic force microscopy on carbon nanowalls. *Journal of Non-Crystalline Solids*, **2012**, 358, 2545-2547 3.9 13
- 104 Conductivity mapping of nanoparticles by torsional resonance tunneling atomic force microscopy. *Applied Physics Letters*, **2012**, 101, 083107 3.4 9
- 103 Position measurement in standing wave interferometer for metrology of length **2011**, 3
- 102 Local photoconductivity of microcrystalline silicon thin films measured by conductive atomic force microscopy. *Physica Status Solidi - Rapid Research Letters*, **2011**, 5, 373-375 2.5 21
- 101 Synthesis, structure, and opto-electronic properties of organic-based nanoscale heterojunctions. *Nanoscale Research Letters*, **2011**, 6, 238 5 21
- 100 Microscopic Characterizations of Nanostructured Silicon Thin Films for Solar Cells. *Materials Research Society Symposia Proceedings*, **2011**, 1321, 313
- 99 Comment on "Current routes in hydrogenated microcrystalline silicon" *Physical Review B*, **2010**, 81, 3.3 15
- 98 The structure and growth mechanism of Si nanoneedles prepared by plasma-enhanced chemical vapor deposition. *Nanotechnology*, **2010**, 21, 415604 3.4 19

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|----|--|-----|----|
| 97 | Photo-conductivity and Hall mobility of holes at polypyrrole/diamond interface. <i>Diamond and Related Materials</i> , 2010 , 19, 174-177 | 3.5 | 7 |
| 96 | Ultrasharp Si nanowires produced by plasma-enhanced chemical vapor deposition. <i>Physica Status Solidi - Rapid Research Letters</i> , 2010 , 4, 37-39 | 2.5 | 13 |
| 95 | Time-resolved opto-electronic properties of poly(3-hexylthiophene-2,5-diyl): Fullerene heterostructures detected by Kelvin force microscopy. <i>Thin Solid Films</i> , 2010 , 519, 836-840 | 2.2 | 8 |
| 94 | High hydrogen dilution and low substrate temperature cause columnar growth of hydrogenated amorphous silicon. <i>Physica Status Solidi (A) Applications and Materials Science</i> , 2010 , 207, 525-529 | 1.6 | 6 |
| 93 | Relation of nanoscale and macroscopic properties of mixed-phase silicon thin films. <i>Physica Status Solidi (A) Applications and Materials Science</i> , 2010 , 207, 582-586 | 1.6 | 8 |
| 92 | Role of the tip induced local anodic oxidation in the conductive atomic force microscopy of mixed phase silicon thin films. <i>Physica Status Solidi C: Current Topics in Solid State Physics</i> , 2010 , 7, NA-NA | | 5 |
| 91 | Ultrafast carrier dynamics in microcrystalline silicon probed by time-resolved terahertz spectroscopy. <i>Physical Review B</i> , 2009 , 79, | 3.3 | 61 |
| 90 | Decomposition of Mixed Phase Silicon Raman Spectra. <i>Materials Research Society Symposia Proceedings</i> , 2009 , 1153, 1 | | |
| 89 | Some controversial points related to transport in microcrystalline silicon. <i>Philosophical Magazine</i> , 2009 , 89, 2557-2571 | 1.6 | 7 |
| 88 | Optoelectronic performance of poly(p-phenylenevinylene)-based heterostructures evaluated by scanning probe techniques. <i>Physica Status Solidi (B): Basic Research</i> , 2009 , 246, 2828-2831 | 1.3 | 2 |
| 87 | LiF enhanced nucleation of the low temperature microcrystalline silicon prepared by plasma enhanced chemical vapour deposition. <i>Thin Solid Films</i> , 2009 , 517, 6829-6832 | 2.2 | 1 |
| 86 | Microcrystalline silicon, grain boundaries and role of oxygen. <i>Solar Energy Materials and Solar Cells</i> , 2009 , 93, 1444-1447 | 6.4 | 14 |
| 85 | Crystallographic properties of grain size-controlled polycrystalline silicon thin films deposited on alumina substrate. <i>Journal of Crystal Growth</i> , 2009 , 311, 789-793 | 1.6 | 2 |
| 84 | Mapping of mechanical stress in silicon thin films on silicon cantilevers by Raman microspectroscopy. <i>Journal of Non-Crystalline Solids</i> , 2008 , 354, 2235-2237 | 3.9 | 5 |
| 83 | Crystallinity of the mixed phase silicon thin films by Raman spectroscopy. <i>Journal of Non-Crystalline Solids</i> , 2008 , 354, 2253-2257 | 3.9 | 34 |
| 82 | A simple quality factor for characterization of thin silicon films. <i>Journal of Non-Crystalline Solids</i> , 2008 , 354, 2227-2230 | 3.9 | 1 |
| 81 | Properties of thin film silicon, prepared at high growth rate in a wide range of thicknesses. <i>Journal of Non-Crystalline Solids</i> , 2008 , 354, 2451-2454 | 3.9 | |
| 80 | Microscopic study of the H ₂ O vapor treatment of the silicon grain boundaries. <i>Journal of Non-Crystalline Solids</i> , 2008 , 354, 2310-2313 | 3.9 | 11 |

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| 79 | Spatially localized current-induced crystallization of amorphous silicon films. <i>Journal of Non-Crystalline Solids</i> , 2008 , 354, 2305-2309 | 3.9 | 9 |
| 78 | Gold Micrometer Crystals Modified with Carboranethiol Derivatives. <i>Journal of Physical Chemistry C</i> , 2008 , 112, 14446-14455 | 3.8 | 42 |
| 77 | C-AFM and X-TEM. <i>Imaging & Microscopy</i> , 2008 , 10, 30-32 | | |
| 76 | A simple tool for quality evaluation of the microcrystalline silicon prepared at high growth rate. <i>Thin Solid Films</i> , 2008 , 516, 4966-4969 | 2.2 | 7 |
| 75 | Correlation of atomic force microscopy detecting local conductivity and micro-Raman spectroscopy on polymerfullerene composite films. <i>Physica Status Solidi - Rapid Research Letters</i> , 2007 , 1, 193-195 | 2.5 | 15 |
| 74 | Controlled growth of nanocrystalline silicon on permalloy micro-patterns. <i>Applied Physics A: Materials Science and Processing</i> , 2007 , 88, 797-800 | 2.6 | 1 |
| 73 | Relation between Electronic Properties and Density of Crystalline Agglomerates in Microcrystalline Silicon. <i>Materials Research Society Symposia Proceedings</i> , 2007 , 989, 1 | | 1 |
| 72 | Structure of mixed-phase Si films studied by C-AFM and X-TEM. <i>Journal of Physics: Conference Series</i> , 2007 , 61, 790-794 | 0.3 | |
| 71 | Surface morphology of spin-coated As ₂ Se ₃ chalcogenide thin films. <i>Journal of Non-Crystalline Solids</i> , 2007 , 353, 1437-1440 | 3.9 | 21 |
| 70 | Internal structure of mixed phase hydrogenated silicon thin films made at 39°C. <i>Applied Physics Letters</i> , 2006 , 89, 051922 | 3.4 | 16 |
| 69 | Properties of Microcrystalline Silicon Prepared at High Growth Rate 2006 , | | 1 |
| 68 | Transport properties of microcrystalline silicon, prepared at high growth rate. <i>Journal of Non-Crystalline Solids</i> , 2006 , 352, 1097-1100 | 3.9 | 10 |
| 67 | Detailed structural study of low temperature mixed-phase Si films by X-TEM and ambient conductive AFM. <i>Journal of Non-Crystalline Solids</i> , 2006 , 352, 1011-1015 | 3.9 | 25 |
| 66 | Characterization of mixed phase silicon by Raman spectroscopy. <i>Journal of Non-Crystalline Solids</i> , 2006 , 352, 1209-1212 | 3.9 | 43 |
| 65 | Microcrystalline silicon prepared at magnetic field modified nucleation. <i>Journal of Non-Crystalline Solids</i> , 2006 , 352, 901-905 | 3.9 | 4 |
| 64 | Annealing in water vapor as a new method for improvement of silicon thin film properties. <i>Journal of Non-Crystalline Solids</i> , 2006 , 352, 955-958 | 3.9 | 9 |
| 63 | Carrier dynamics in microcrystalline silicon studied by time-resolved terahertz spectroscopy. <i>Journal of Non-Crystalline Solids</i> , 2006 , 352, 2846-2849 | 3.9 | 6 |
| 62 | Characterization of hydrogen contained in passivated poly-Si and microcrystalline-Si by ERDA technique. <i>Surface and Interface Analysis</i> , 2006 , 38, 819-822 | 1.5 | 2 |

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|----|--|-----|----|
| 61 | Defects generation by hydrogen passivation of polycrystalline silicon thin films. <i>Solar Energy</i> , 2006 , 80, 653-657 | 6.8 | 11 |
| 60 | Hydrogenation of polycrystalline silicon thin films. <i>Thin Solid Films</i> , 2006 , 501, 144-148 | 2.2 | 7 |
| 59 | Characterization of grain growth, nature and role of grain boundaries in microcrystalline silicon. Review of typical features. <i>Thin Solid Films</i> , 2006 , 501, 107-112 | 2.2 | 29 |
| 58 | Effect of hydrogen passivation on polycrystalline silicon thin films. <i>Thin Solid Films</i> , 2005 , 487, 152-156 | 2.2 | 27 |
| 57 | Patterning of hydrogenated microcrystalline silicon growth by magnetic field. <i>Applied Physics Letters</i> , 2005 , 87, 011901 | 3.4 | 8 |
| 56 | Thin silicon films deposited at low substrate temperatures studied by surface photovoltage technique. <i>Thin Solid Films</i> , 2004 , 451-452, 408-412 | 2.2 | |
| 55 | The physics and technological aspects of the transition from amorphous to microcrystalline and polycrystalline silicon. <i>Physica Status Solidi C: Current Topics in Solid State Physics</i> , 2004 , 1, 1097-1114 | | 23 |
| 54 | Model of electronic transport in microcrystalline silicon and its use for prediction of device performance. <i>Journal of Non-Crystalline Solids</i> , 2004 , 338-340, 303-309 | 3.9 | 29 |
| 53 | Photogenerated carriers in μ -Si:H/a-Si:H multi-layers. <i>Journal of Non-Crystalline Solids</i> , 2004 , 338-340, 353-356 | 3.9 | 8 |
| 52 | Formation of microcrystalline silicon at low temperatures and role of hydrogen. <i>Journal of Non-Crystalline Solids</i> , 2004 , 338-340, 287-290 | 3.9 | 7 |
| 51 | Structure and Properties of Silicon Thin Films Deposited at Low Substrate Temperatures. <i>Japanese Journal of Applied Physics</i> , 2003 , 42, L987-L989 | 1.4 | 6 |
| 50 | Silicon thin films deposited at very low substrate temperatures. <i>Thin Solid Films</i> , 2003 , 442, 163-166 | 2.2 | 4 |
| 49 | Basic features of transport in microcrystalline silicon. <i>Solar Energy Materials and Solar Cells</i> , 2003 , 78, 493-512 | 6.4 | 54 |
| 48 | Surface photovoltage measurements in μ -Si:H: Manifestation of the bottom space charge region. <i>Journal of Applied Physics</i> , 2002 , 92, 2323-2329 | 2.5 | 5 |
| 47 | Rapid crystallization of amorphous silicon at room temperature. <i>The Philosophical Magazine: Physics of Condensed Matter B, Statistical Mechanics, Electronic, Optical and Magnetic Properties</i> , 2002 , 82, 1785-1793 | | 20 |
| 46 | Microcrystalline silicon thin films studied by atomic force microscopy with electrical current detection. <i>Journal of Applied Physics</i> , 2002 , 92, 587-593 | 2.5 | 70 |
| 45 | Role of grains in protocrystalline silicon layers grown at very low substrate temperatures and studied by atomic force microscopy. <i>Journal of Non-Crystalline Solids</i> , 2002 , 299-302, 767-771 | 3.9 | 29 |
| 44 | Influence of combined AFM/current measurement on local electronic properties of silicon thin films. <i>Journal of Non-Crystalline Solids</i> , 2002 , 299-302, 360-364 | 3.9 | 13 |

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|----|--|-----|-----|
| 43 | Importance of the transport isotropy in μ -Si:H thin films for solar cells deposited at low substrate temperatures. <i>Journal of Non-Crystalline Solids</i> , 2002 , 299-302, 395-399 | 3.9 | 9 |
| 42 | Model of transport in microcrystalline silicon. <i>Journal of Non-Crystalline Solids</i> , 2002 , 299-302, 355-359 | 3.9 | 38 |
| 41 | Detection of bottom depletion layer and its influence on surface photovoltage measurement in μ -Si:H. <i>Thin Solid Films</i> , 2001 , 383, 271-273 | 2.2 | 4 |
| 40 | Charge transport in microcrystalline Si μ the specific features. <i>Solar Energy Materials and Solar Cells</i> , 2001 , 66, 61-71 | 6.4 | 20 |
| 39 | Microcrystalline Silicon - Relation between Transport and Microstructure. <i>Solid State Phenomena</i> , 2001 , 80-81, 213-224 | 0.4 | 17 |
| 38 | Amorphous/microcrystalline silicon superlattices μ the chance to control isotropy and other transport properties. <i>Applied Physics Letters</i> , 2001 , 79, 2540-2542 | 3.4 | 17 |
| 37 | A new approach to surface photovoltage measurements on hydrogenated microcrystalline silicon layers. <i>Philosophical Magazine Letters</i> , 2001 , 81, 405-410 | 1 | 5 |
| 36 | Transport anisotropy in microcrystalline silicon studied by measurement of ambipolar diffusion length. <i>Journal of Applied Physics</i> , 2001 , 89, 1800 | 2.5 | 29 |
| 35 | Microscopic Aspects Of Charge Transport In Hydrogenated Microcrystalline Silicon. <i>Materials Research Society Symposia Proceedings</i> , 2001 , 664, 1611 | | 11 |
| 34 | Surface and bulk light scattering in microcrystalline silicon for solar cells. <i>Journal of Non-Crystalline Solids</i> , 2000 , 271, 152-156 | 3.9 | 8 |
| 33 | New method of drift mobility evaluation in μ -Si:H, basic idea and comparison with time-of-flight. <i>Journal of Non-Crystalline Solids</i> , 2000 , 266-269, 331-335 | 3.9 | 17 |
| 32 | Anisotropic carrier transport in preferentially oriented polycrystalline silicon films fabricated by very-high-frequency plasma enhanced chemical vapor deposition using fluorinated source gas. <i>Journal of Non-Crystalline Solids</i> , 2000 , 266-269, 341-346 | 3.9 | 6 |
| 31 | Local electronic transport in microcrystalline silicon observed by combined atomic force microscopy. <i>Journal of Non-Crystalline Solids</i> , 2000 , 266-269, 309-314 | 3.9 | 7 |
| 30 | Optical absorption and light scattering in microcrystalline silicon thin films and solar cells. <i>Journal of Applied Physics</i> , 2000 , 88, 148-160 | 2.5 | 205 |
| 29 | Local characterization of electronic transport in microcrystalline silicon thin films with submicron resolution. <i>Applied Physics Letters</i> , 1999 , 74, 1475-1477 | 3.4 | 68 |
| 28 | Microcrystalline Silicon - Relation of Transport Properties and Microstructure. <i>Materials Research Society Symposia Proceedings</i> , 1999 , 557, 483 | | 20 |
| 27 | Characterization of Laser Patterned a-Si:H Thin Films by Combined AFM/Local Current Measurements. <i>Physica Status Solidi A</i> , 1998 , 170, R1-R2 | | 7 |
| 26 | Thin nanocomposite films of phthalocyanines and metals. <i>Vacuum</i> , 1998 , 50, 191-194 | 3.7 | 3 |

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| 25 | Reexamination of high drift mobility a-Si:H. <i>Journal of Non-Crystalline Solids</i> , 1998 , 227-230, 229-232 | 3.9 | 1 |
| 24 | Properties of amorphous carbon films characterized by laser desorption time of flight mass spectroscopy. <i>Journal of Non-Crystalline Solids</i> , 1998 , 227-230, 632-635 | 3.9 | 1 |
| 23 | On the transport properties of microcrystalline silicon. <i>Journal of Non-Crystalline Solids</i> , 1998 , 227-230, 1006-1010 | 3.9 | 23 |
| 22 | Electroluminescent properties of a-SiO _x :H alloys. <i>Journal of Non-Crystalline Solids</i> , 1998 , 227-230, 1160-1163 | 3.9 | 1 |
| 21 | Short-term degradation of porous silicon light-emitting diodes. <i>Journal of Luminescence</i> , 1997 , 72-74, 992-993 | 3.8 | |
| 20 | Nanostructural composites of phthalocyanine and metals. <i>European Physical Journal D</i> , 1997 , 47, 461-465 | | 1 |
| 19 | Comments on space-charge-limited time-of-flight measurements in post-transit mode, applied to a-Si:H based solar cells. <i>Journal of Non-Crystalline Solids</i> , 1996 , 198-200, 190-193 | 3.9 | 5 |
| 18 | Precise measurement of the deep defects and surface states in a-Si:H films by absolute CPM. <i>Journal of Non-Crystalline Solids</i> , 1996 , 198-200, 304-308 | 3.9 | 11 |
| 17 | Light emitting silicon, recent progress. <i>Journal of Non-Crystalline Solids</i> , 1996 , 198-200, 857-862 | 3.9 | 27 |
| 16 | Optical and Electrical Properties of Undoped Microcrystalline Silicon Deposited by the VHF-GD with Different Dilutions of Silane in Hydrogen. <i>Materials Research Society Symposia Proceedings</i> , 1996 , 452, 761 | | 17 |
| 15 | Charge transport in porous silicon: considerations for achievement of efficient electroluminescence. <i>Thin Solid Films</i> , 1996 , 276, 187-190 | 2.2 | 20 |
| 14 | Instabilities in electroluminescent porous silicon diodes. <i>Applied Physics Letters</i> , 1996 , 69, 833-835 | 3.4 | 13 |
| 13 | Electric and Photoelectric Properties of High Porosity Silicon. <i>Physica Status Solidi (B): Basic Research</i> , 1995 , 190, 27-33 | 1.3 | 10 |
| 12 | Characterization of carbon nitride films prepared by laser reactive ablation deposition. <i>Journal of Electron Spectroscopy and Related Phenomena</i> , 1995 , 76, 747-752 | 1.7 | 24 |
| 11 | Light-emitting Si prepared by laser annealing of a-Si:H. <i>Thin Solid Films</i> , 1995 , 255, 302-304 | 2.2 | 3 |
| 10 | Direct measurement of the deep defect density in thin amorphous silicon films with the "Absolute" constant photocurrent method. <i>Journal of Applied Physics</i> , 1995 , 78, 6203-6210 | 2.5 | 75 |
| 9 | Transport study of self-supporting porous silicon. <i>Applied Physics Letters</i> , 1995 , 66, 1098-1100 | 3.4 | 36 |
| 8 | Hydrogen and nitrogen bonding in silicon nitride layers deposited by laser reactive ablation: Infrared and x-ray photoelectron study. <i>Applied Physics Letters</i> , 1995 , 67, 3269-3271 | 3.4 | 16 |

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| 7 | Photoconductivity study of self-supporting porous silicon. <i>Thin Solid Films</i> , 1995 , 255, 269-271 | 2.2 | 19 |
| 6 | Metal-doped hard carbon films. <i>International Journal of Electronics</i> , 1994 , 76, 937-940 | 1.2 | 4 |
| 5 | Thin films prepared by simultaneous deposition of copper and free-base phthalocyanine. <i>European Physical Journal D</i> , 1993 , 43, 905-909 | | 3 |
| 4 | Ion cluster beam deposition of phthalocyanine films. <i>International Journal of Electronics</i> , 1992 , 73, 1051-1053 | 1.2 | 3 |
| 3 | Plasma polymerized PVCa and composite Au/PVCa films and their physical properties. This paper was presented at the Second International Seminar on the Electronic Properties of Metal/Non-metal Microsystems, held at Žilina, Czechoslovakia, 18-22 September 1989, but missed the deadline for publication in the July 1990 Special Issue of the International Journal of | 1.2 | 3 |
| 2 | Temperature induced structural rearrangements of Ag/a-C:H composite films and their dc electrical conduction. <i>Vacuum</i> , 1990 , 40, 377-380, 70, 509-513 | 3.7 | 12 |
| 1 | Microstructure and optical properties of gold - doped plasma polymerized halocarbons. <i>Vacuum</i> , 1989 , 39, 19-22 | 3.7 | 10 |